XBS303V17R-G is Discontinued. XBS303V17R-G

Schottky Barrier Diode, 3A, 30V Type

■FEATURES

Forward Voltage	: V _F =0.355V (TYP.)			
Forward Current	: I _{F(AVE)} =3A			
Repetitive Peak Reverse Voltage	: V _{RM} =30V			

■ABSOLUTE MAXIMUM RATINGS

UNIT V V	
V V	
V	
А	
^	
A	
°C	
°C	

*1 : Non continuous high amplitude 60Hz half-sine wave.

* When the IC is operated continuously under high load conditions such as high temperature, high current and high voltage, it may have the case that reliability reduces drastically even if under the absolute maximum ratings. Adequate "Derating" should be taken into consideration while designing.

MARKING RULE



①②③④⑤⑥: 303V17(Product Number) ⑦⑧ : Assembly Lot Number

■PRODUCT NAME

PRODUCT NAME	DEVICE ORIENTATION
XBS303V17R-G	SMA (Halogen & Antimony free)
XBS303V17R	SMA

* The "-G" suffix indicates that the products are Halogen and Antimony free as well as being fully RoHS compliant.

* The device orientation is fixed in its embossed tape pocket.

ELECTRICAL CHARACTERISTICS

PARAMETER SY	SYMBOL		LIMITS			UNIT
	STIVIDUL	SYMBOL TEST CONDITIONS		TYP.	MAX.	UNIT
Forward Voltage	VF1	I _F =0.5A	-	0.265	0.34	V
	VF2	I _F =1A	-	0.295	0.36	V
	VF3	I _F =3A	-	0.355	0.39	V
Reverse Current	IR	V _R =30V	-	0.35	3	mA
Inter-Terminal Capacity	Ct	V _R =1V , f=1MHz	-	385	-	pF
Reverse Recovery Time*2	trr	I _F =I _R =10mA , irr=1mA	-	90	-	ns

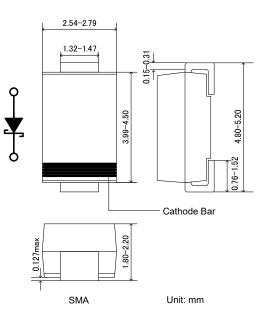
*2 : trr measurement circuit

Circuit Bias Device Under test Pulse Generatrix Oscilloscope

■ APPLICATIONS

- Rectification
- Protection against reverse connection of battery

■ PACKAGING INFORMATION



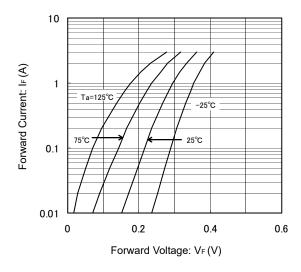
Ta=25°C

XBS303V17R-G

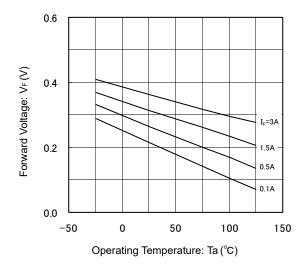
■TYPICAL PERFORMANCE CHARACTERISTICS

(1) Forward Current vs. Forward Voltage

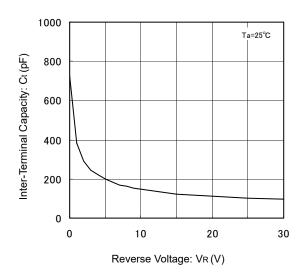
(2) Reverse Current vs. Reverse Voltage

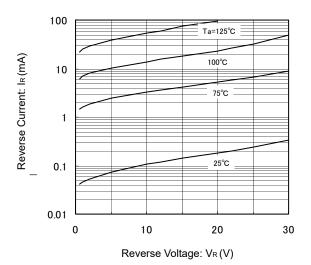


(3) Forward Voltage vs. Operating Temperature

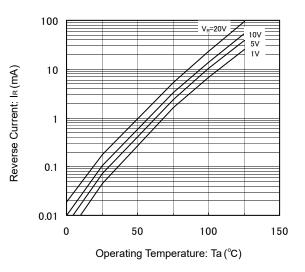


(5) Inter-Terminal Capacity vs. Reverse Voltage

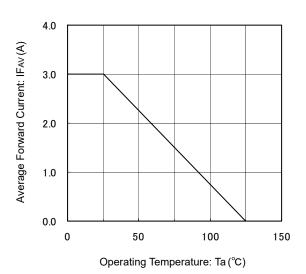




(4) Reverse Current vs. Operating Temperature



(6) Average Forward Current vs. Operating Temperature



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